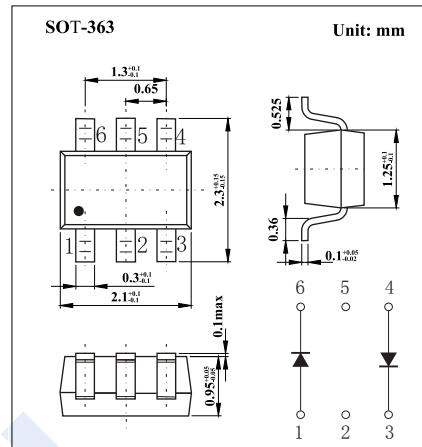


Switching Diodes

MMBD4448DW (KMBD4448DW)

■ Features

- Fast Switching Speed
- For General Purpose Switching Applications.
- High Conductance
- Ultra-Small Surface Mount Package



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Reverse Voltage	V _{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V _{RRM}		
Working Peak Reverse Voltage	V _{RWM}	75	
DC Blocking Voltage	V _R		
RMS Reverse Voltage	V _{R(RMS)}	53	
Average Rectified Output Current	I _O	250	mA
Forward Continuous Current	I _{FM}	500	
Peak Forward Surge Current @ t=1.0us @t =1s	I _{FSM}	4 1.5	A
Power Dissipation	P _d	200	mW
Thermal Resistance Junction to Ambient	R _{θ JA}	625	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V _R	I _R = 100 μA	75			V
Forward voltage	V _{F1}	I _F = 5 mA	0.62		0.72	
	V _{F2}	I _F = 10 mA			0.855	
	V _{F3}	I _F = 50 mA			1	
	V _{F4}	I _F = 150 mA			1.25	
Reverse voltage leakage current	I _{R1}	V _R = 75 V			2.5	uA
	I _{R2}	V _R = 75 V, T _J = 150°C			50	
	I _{R3}	V _R = 25 V, T _J = 150°C			30	
	I _{R4}	V _R = 20 V			25	nA
Junction capacitance	C _j	V _R = 0 V, f= 1 MHz			4	pF
Reverse recovery time	t _{rr}	I _f =I _R =10 mA, I _{rr} =0.1×I _R , R _L =100Ω			4	ns

■ Marking

Marking	KA3
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